

Fangfei Ming

List of Publications by Year in descending order

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1040056

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docs citations

22

times ranked

291

citing authors

#	ARTICLE	IF	CITATIONS
1	Realization of a Hole-Doped Mott Insulator on a Triangular Silicon Lattice. <i>Physical Review Letters</i> , 2017, 119, 266802.	7.8	33
2	Assembling and Disassembling Ag Clusters on Si(111)-(7 Å–7) by Vertical Atomic Manipulation. <i>ACS Nano</i> , 2011, 5, 7608-7616.	14.6	30
3	Superconductivity in a Hole-Doped Mott-Insulating Triangular Adatom Layer on a Silicon Surface. <i>Physical Review Letters</i> , 2020, 125, 117001.	7.8	26
4	Stabilization and Manipulation of Electronically Phase-Separated Ground States in Defective Indium Atom Wires on Silicon. <i>Physical Review Letters</i> , 2014, 113, 196802.	7.8	22
5	Hidden phase in a two-dimensional Sn layer stabilized by modulation hole doping. <i>Nature Communications</i> , 2017, 8, 14721.	12.8	17
6	Electrical rectification by selective wave-function coupling in small Ag clusters on $\text{Si}(111)$. <i>Physical Review B</i> , 2010, 81, .	8.2	11
7	Identifying the Numbers of Ag Atoms in Their Nanostructures Grown on a Si(111)-(7 Å–7) Surface. <i>Journal of Physical Chemistry C</i> , 2011, 115, 3847-3853.	3.1	11
8	Zero-bias anomaly in nanoscale hole-doped Mott insulators on a triangular silicon surface. <i>Physical Review B</i> , 2018, 97, .	3.2	11
9	Equivalence of electronic and mechanical stresses in structural phase stabilization: A case study of indium wires on Si(111). <i>Physical Review B</i> , 2015, 91, .	3.2	10
10	Size-dependent superconducting state of individual nanosized Pb islands grown on Si(111) by tunneling spectroscopy. <i>Journal of Physics Condensed Matter</i> , 2011, 23, 265007.	1.8	9
11	Study of CO diffusion on stepped Pt(111) surface by scanning tunneling microscopy. <i>Surface Science</i> , 2010, 604, 322-326.	1.9	8
12	Superconductivity of individual Pb islands on Si(111): pseudogap, critical region, density of states, and island size. <i>Superconductor Science and Technology</i> , 2013, 26, 085009.	3.5	8
13	Coupled Sublattice Melting and Charge-Order Transition in Two Dimensions. <i>Physical Review Letters</i> , 2020, 124, 097602.	7.8	8
14	Probing the generalized magicity of Ag nanoclusters constructed on Si(111) by atomic manipulation. <i>Physical Review B</i> , 2013, 88, .	3.2	7
15	Controllable dissociations of PH ₃ molecules on Si(001). <i>Nanotechnology</i> , 2016, 27, 135704.	2.6	7
16	Controlling adsorption and spin configurations of Co atoms on $\text{Si}(111)$. <i>Physical Review B</i> , 2015, 91, .	3.2	7
17	Interface effects on the quantum well states of Pb thin films. <i>Journal of Physics Condensed Matter</i> , 2011, 23, 485001.	1.8	5
18	Effect of substrate doping concentration on quantum well states of Pb island grown on Si(111). <i>Surface Science</i> , 2010, 604, 175-180.	1.9	4

#	ARTICLE	IF	CITATIONS
19	Atomic and electronic structure of doped $\text{Si}_{1-x}\text{Sn}_x$ interfaces. Physical Review B, 2018, 97, .		
20	Adsorption and spin-related properties of multi-Co atoms assembled in the half unit cells of Si(111)-(7 Å)–Tj ETQq0g0rgBT3/Overlock		
21	Mapping potential energy landscape of a probing atom in a complex surface environment. Physical Review B, 2015, 92, .	3.2	2
22	Controlled Implantation of Phosphorous Atoms into a Silicon Surface Lattice with a Scanning Tunneling Microscopy Tip. ACS Applied Electronic Materials, 2021, 3, 3338-3345.	4.3	1